

Trench MOS Barrier Schottky Rectifier - 3Amp 40Volt

Features

- For surface mounted applications
- Low profile package
- Built-in strain relief
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High temperature soldering guaranteed
- High reliability
- High surge current capability
- Epitaxial construction
- Lead free device
- Halogen-Free

Mechanical data

- Case : Molded plastic
- Epoxy : UL 94V-0 rate flame retardant
- Terminals : Solder plated, solderable per MIL-STD-750,method 2026
- Polarity : Color band denotes cathode end
- Weight : 0.003 ounce 0.0955 grams

Maximum ratings and Electrical characteristics

| Parameters | SBR3V4 | UNIT |
|--|-------------|------|
| Maximum Recurrent Peak Reverse Voltage | 40 | V |
| Maximum RMS Voltage | 28 | V |
| Maximum DC Blocking Voltage | 40 | V |
| Maximum Average Forward Rectified Current | 3 | A |
| Peak Forward Surge Current | 80 | A |
| Maximum Instantaneous Forward Voltage at 3A | Tc = 25°C | V |
| | Tc = 125°C | |
| Maximum Average Reverse Current at Rated DC Blocking Voltage | Tc = 25°C | mA |
| | Tc = 125°C | |
| Typical Junction Capacitance | 500 | pF |
| Typical Thermal Resistance R _{θJL} (Note 1) | 18 | °C/W |
| Operating and Storage Temperature Range | -50 to +150 | °C |

Note : 1. Mounted on P.C.B with copper pad size 14mm x 14mm

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SBR3V4

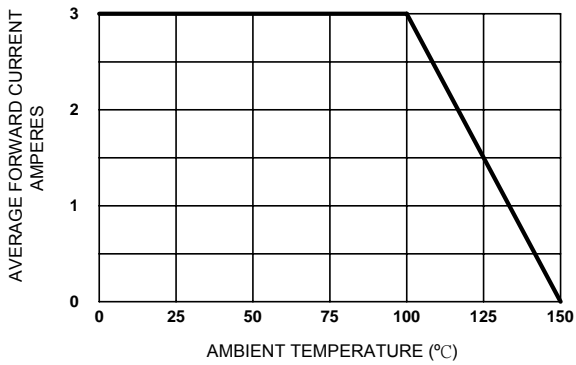


Figure 1. Forward Current Derating Curve

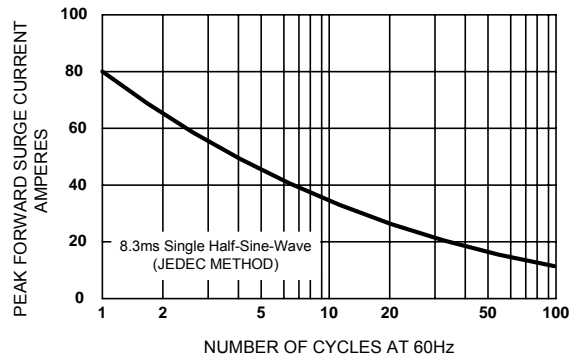


Figure 2. Maximum Non-repetitive Surge Current

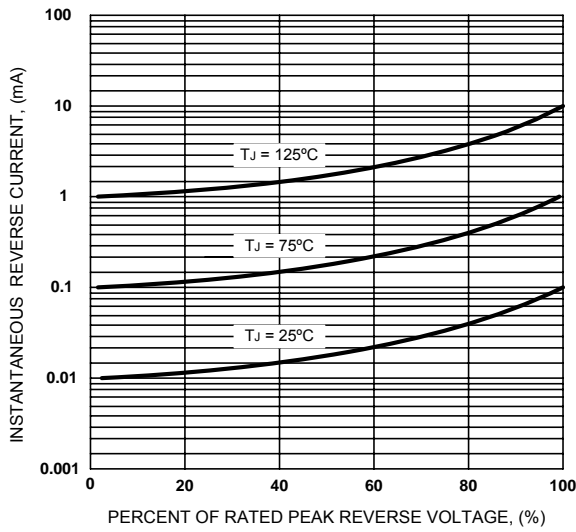


Figure 3. Typical Reverse Characteristics

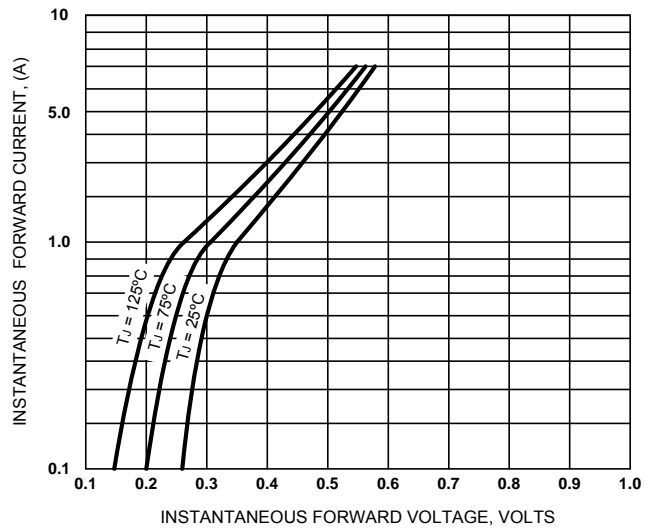


Figure 4. Typical Forward Characteristics

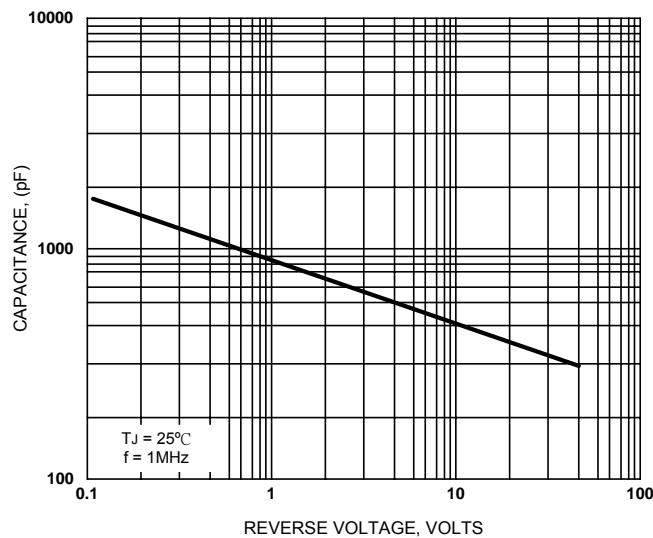
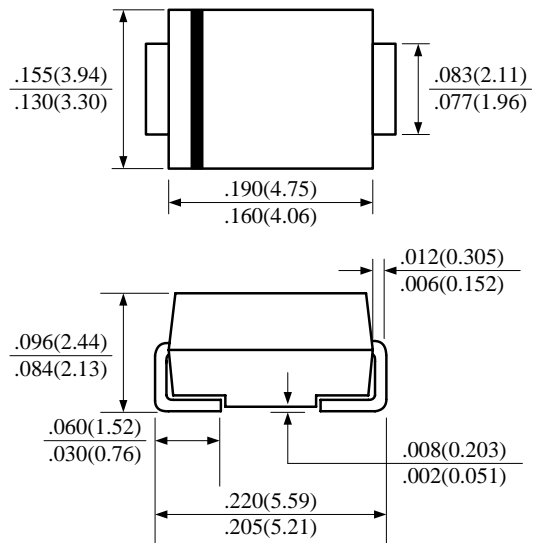


Figure 5. Typical Junction Capacitance

SBR3V4

SMB



UNIT : inch(mm)

